

IN THE SPECIFICATION

Paragraph starting at page 1, line 7:

In the fabrication of a semiconductor integrated circuit, an insulating film made from SiO₂ etc., and a protective film made of a nitride film made from Si₃N₄ etc. are generally formed by the plasma CVD (Chemical Vapor Deposition) method (refer to patent document, for example, JP, H 11 – 214670, A) or a thermal CVD method such as the LP (Low Pressure) CVD method, and so forth. For example, the nitride film made from Si₃N₄ is formed by the LP CVD method carried out at a high reaction temperature in the range of 800 to 900°C by use of dichlorosilane gas and ammonia gas as stock gases. Incidentally, the following U. S. applications for Letters patent relating to a method of fabricating an insulating film by use of vacuum ultraviolet rays, which are commonly assigned with this application, have been submitted to U. S. PTO by the assignee of the inventor of this application: Ser. Nos. 09/798,930, 09/833,646, 10/052,243, 10/059,174, and 10/105,382.

Sole paragraph on page 25:

In a method of fabricating a protective film, a vacuum ultraviolet radiation CVD (Chemical Vapor Deposition) system is provided used. The system method includes providing a vacuum ultraviolet rays generator, a reactor provided with a platform for supporting a substrate, a heat retainer provided on the platform, and a window separating the vacuum ultraviolet rays generator from the reactor. Then, a step of feeding an organic stock gas is fed from a gas feeder into the reactor while retaining the temperature of the substrate at a [[low]] temperature of about equal to or less than 100 °C with the heat retainer is performed. Simultaneously, a step of irradiating the reactor is irradiated with vacuum ultraviolet rays from the vacuum ultraviolet rays generator through the window is performed.